

Customer No.: 31561  
Application No.: 10/711,574  
Docket NO.: 13504-US-PA

**In The Specification:**

Please amend paragraph [0047] as follows:

[0047] Referring to Fig. 5D and Fig. 2, the semiconductor material layer 223 (as shown in Fig. 5C) is patterned to form a semiconductor strip 228b in the trench 218. The semiconductor strip 228b is shown in Fig. 2. In one preferred embodiment, a portion of the mask layer 204, the pad layer 202 and the substrate 200 are removed to form two openings (enclosed area 226 by dash line in Fig. 2) that expose the substrate 200. In another preferred embodiment, the process of forming the semiconductor strip 228b in the trench 218 further includes forming extension portions 228a and 228c on each end of the semiconductor strip 228b to form an H-shaped semiconductor layer 224. The extension portion 228a is adjacent to the conductive layer 216 while the other extension portion 228c is adjacent to the substrate 200. The semiconductor strip 228b and its extension portions 228a and 228c are fabricated using, for example, epitaxial silicon or other semiconductor material suitable for forming a channel.